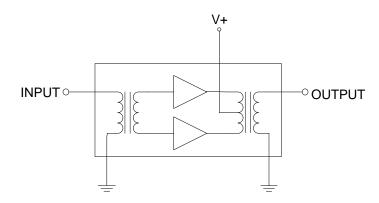


RFPD2710

GaAs/GaN Power Doubler Hybrid 45MHz to 1003MHz

The RFPD2710 is a Hybrid Power Doubler amplifier module. The part employs GaAs pHEMT die and GaN HEMT die, has high output capability, and is operated from 45MHz to 1003MHz. It provides excellent linearity and superior return loss performance with low noise and optimal reliability.





Package: SOT-115J

Features

- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Low Noise
- Unconditionally Stable Under All Terminations
- Extremely High Output Capability
- 24.5dB Min. Gain at 1003MHz
- 450mA Max. at 24V_{DC}

Applications

 45MHz to 1003MHz CATV Amplifier Systems

Ordering Information

RFPD2710 Box with 50 Pieces

Absolute Maximum Ratings

Parameter	Rating	Unit
RF Input Voltage (single tone)	60	dBmV
DC Supply Over-Voltage (5 minutes)	30	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C



Caution! ESD sensitive device.



RoHS (Restriction of Hazardous Substances): Compliant per EU Directive 2011/65/EU.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.



Nominal Operating Parameters

Parameter	Specification		Unit	Condition		
raiailietei	Min	Тур	Max	Onit	Condition	
General Performance					$V+ = 24V; T_{MB} = 30^{\circ}C; Z_{S} = Z_{L} = 75\Omega$	
Power Gain	23.3	23.8	24.3	dB	f = 45MHz	
	24.5	25.0	26.0	dB	f = 1003MHz	
Slope ^[1]	0.5	1.0	2.0	dB	f = 45MHz to 1003MHz	
Flatness of Frequency Response			0.8	dB	f = 45MHz to 1003MHz	
Input Return Loss	20			dB	f = 45MHz to 320MHz	
	19			dB	f = 320MHz to 640MHz	
	18			dB	f = 640MHz to 870MHz	
	16			dB	f = 870MHz to 1003MHz	
Output Return Loss	20			dB	f = 45MHz to 320MHz	
	19			dB	f = 320MHz to 640MHz	
	18			dB	f = 640MHz to 870MHz	
	17			dB	f = 870MHz to 1003MHz	
Noise Figure		3.0	4.0	dB	f = 50MHz to 1003MHz	
Total Current Consumption (DC)		420.0	450.0	mA		
Distortion Data 40MHz to 550MHz					$V+ = 24V$; $T_{MB} = 30$ °C; $Z_{S} = Z_{L} = 75\Omega$	
СТВ		-77	-74	dBc	V_{O} = 56.4dBmV at 1000MHz, 13.4dB extrapolated tilt, 79 analog channels plus 75 digital channels (-6dB offset) ^[2]	
XMOD		-71	-68	dBc		
CSO		-71	-68	dBc		
CIN	63	66		dB		

^{1.} The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.

Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA.

Composite Triple Beat (CTB) - The CTB parameter is defined by the NCTA.

Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested.

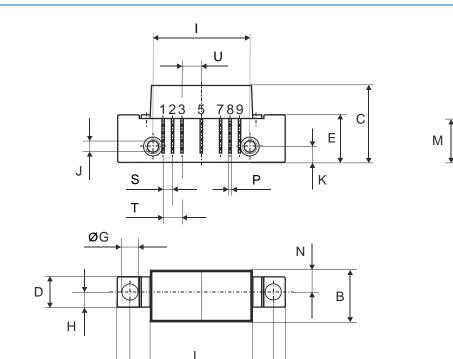
Carrier to Intermodulation Noise (CIN) - The CIN parameter is defined by ANSI/SCTE 17 (Test procedure for carrier to noise).

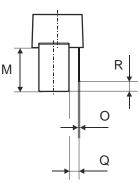
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^{2. 79} analog channels, NTSC frequency raster: 55.25MHz to 547.25MHz, +43dBmV to +50dBmV tilted output level, plus 75 digital channels, -6dB offset relative to the equivalent analog carrier.



Package Drawing (Dimensions in millimeters)





5 10mm لسلسا scale

Notes:

European Projection

F

Α



Pinning:

Pin	Name
1	Input
2-3	GND
4	
5	V+
6	
7-8	GND
9	Output

	Nominal	Min	Max
Α	44,6 ^{± 0,2}	13,4 _{.,4}	44,8
В	13,6 ^{± 0,2}	13,4	13,8
С	20,4 ^{± 0,5}	19,9	20,9
D	8 ^{± 0,15}	7,85	8,15
Е	12,6 ^{± 0,15}	12,45	12,75
F	38,1 ^{± 0,2}	37,9	38,3
G	4 +0,2 / -0,05	3,95	4,2
Н	4 ^{± 0,2}	3,8	4,2
I	25,4 ^{± 0,2}	25,2	25,6
J	UNC 6-32	-	-
K	4,2 ^{± 0,2}	4,0	4,4
L	27,2 ^{± 0,2}	27,0	27,4
М	11,6 ^{± 0,5}	11,1	12,1
N	5,8 ^{± 0,4}	5,4	6,2
0	0,25 ^{± 0,02}	0,23	0,27
Р	0,45 ^{± 0,03}	0,42	0,48
Q	2,54 ^{± 0,3}	2,24	2,84
R	2,54 ^{± 0,5}	2,04	3,04
S	2,54 ^{± 0,25}	2,29	2,79
Т	5,08 ^{± 0,25}	4,83	5,33
U	5,08 ^{± 0,25}	4,83	5,33